

# N-Channel 20 V (D-S) MOSFET

## PRODUCT SUMMARY

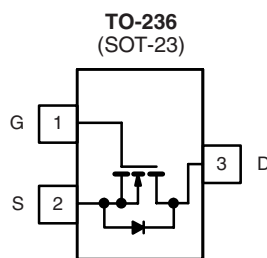
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)	$Q_g$ (Typ.)
20	0.031 at $V_{GS} = 4.5$ V	5.0	7.5
	0.037 at $V_{GS} = 2.5$ V	4.6	
	0.047 at $V_{GS} = 1.8$ V	4.1	

## FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 %  $R_g$  Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available



Top View

Si2312BDS (M2)\*

\* Marking Code

Ordering Information: Si2312BDS-T1-E3 (Lead (Pb)-free)  
Si2312BDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

## ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	20		V
Gate-Source Voltage		V <sub>GS</sub>	± 8		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	5.0	3.9	A
	T <sub>A</sub> = 70 °C		4.0	3.1	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	15		
Avalanche Current <sup>b</sup>	L = 0.1 mH	I <sub>AS</sub>	13		
Single Avalanche Energy		E <sub>AS</sub>	8.45		mJ
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	1.0	0.63	A
Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	1.25	0.75	W
	T <sub>A</sub> = 70 °C		0.80	0.48	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	80	100	°C/W
		120	166	
Maximum Junction-to-Foot	$R_{thJF}$	50	60	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.

**SPECIFICATIONS**  $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted

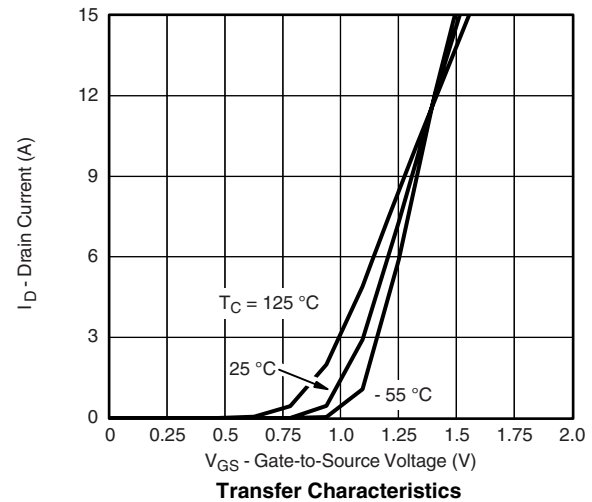
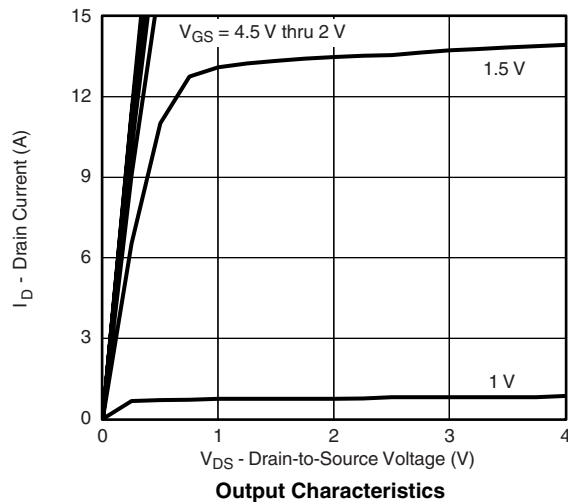
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	20			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.45		0.85	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			75	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 10 V, V <sub>GS</sub> = 4.5 V	15			A
Drain-Source On-Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5.0 A		0.025	0.031	Ω
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 4.6 A		0.030	0.037	
		V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 4.1 A		0.036	0.047	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 5.0 A		30		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1.0 A, V <sub>GS</sub> = 0 V		0.8	1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5.0 A		7.5	12	nC
Gate-Source Charge	Q <sub>gs</sub>			1.4		
Gate-Drain Charge	Q <sub>gd</sub>			1.2		
Gate Resistance	R <sub>g</sub>	f = 1.0 MHz	1.1	2.2	3.3	Ω
Switching						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10 V, R <sub>L</sub> = 10 Ω I <sub>D</sub> ≅ 1.0 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 6 Ω		9	15	ns
Rise Time	t <sub>r</sub>			30	45	
Turn-Off Delay Time	t <sub>d(off)</sub>			35	55	
Fall Time	t <sub>f</sub>			10	15	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1.0 A, dI/dt = 100 A/μs		13	25	nC
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			4.5	7	

Notes:

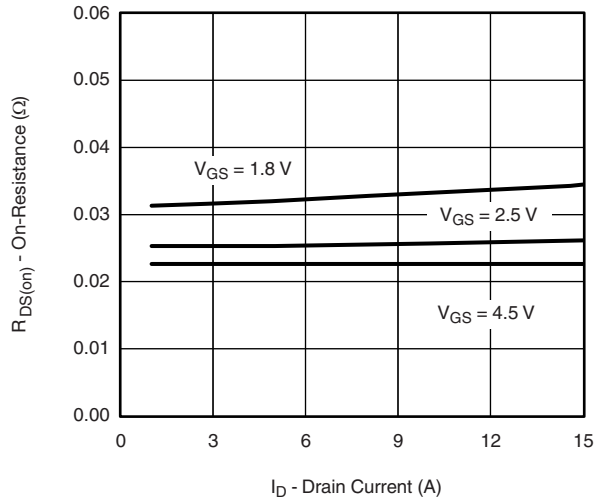
a. Pulse test: Pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

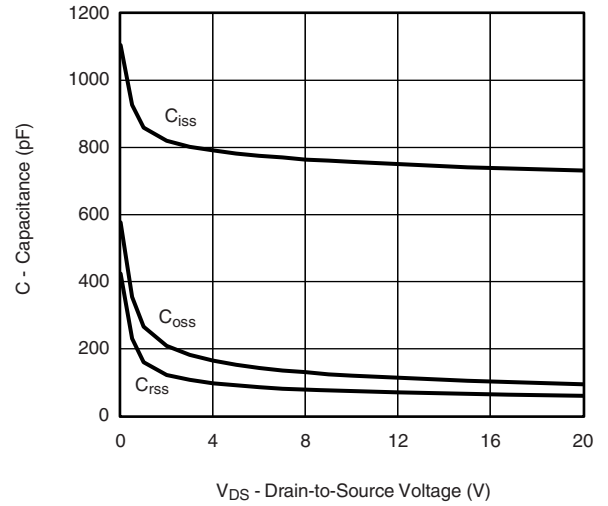
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS**  $25\text{ }^{\circ}\text{C}$ , unless otherwise noted

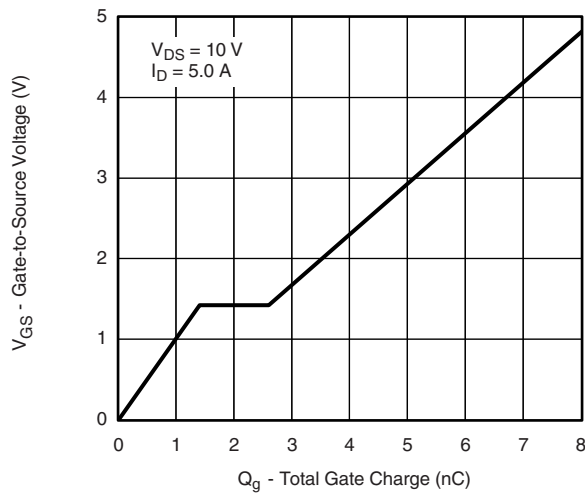
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



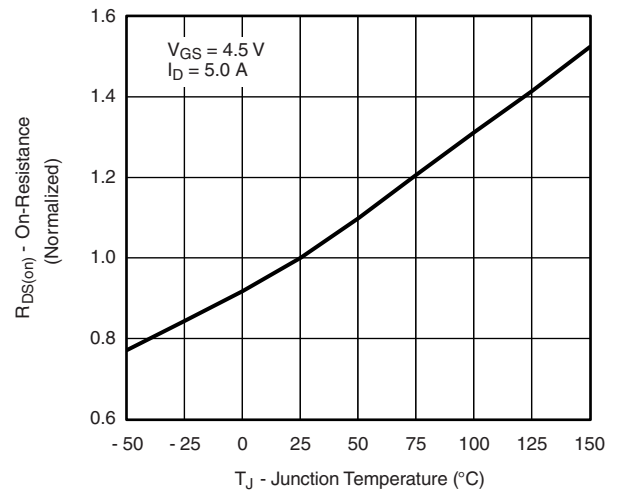
On-Resistance vs. Drain Current



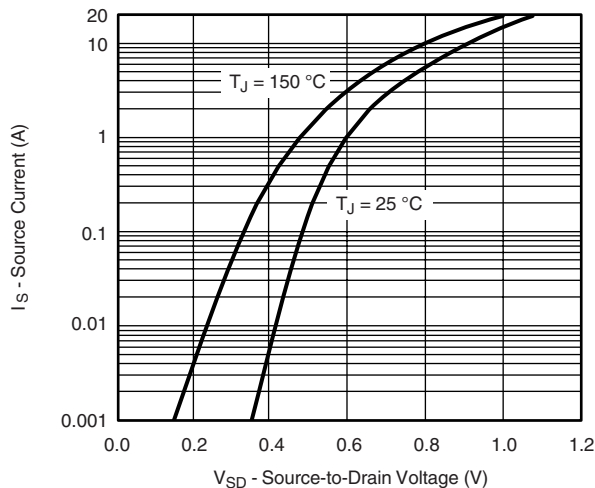
Capacitance



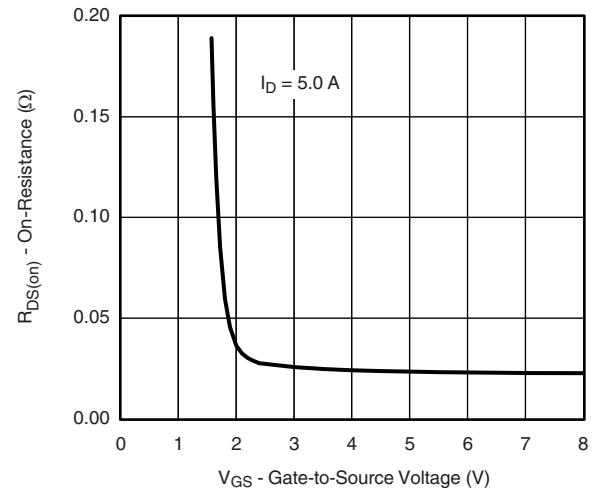
Gate Charge



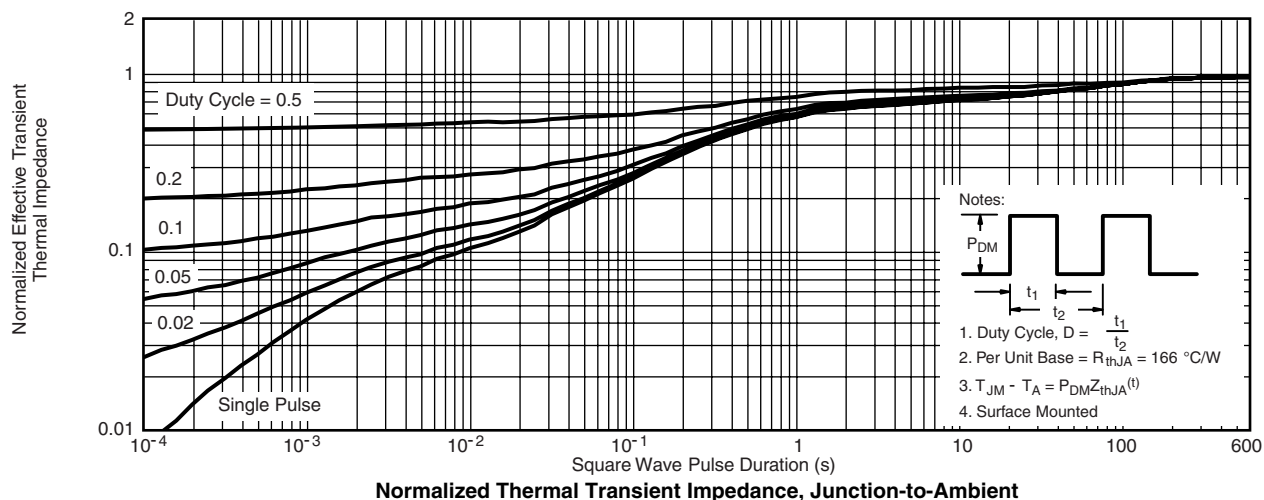
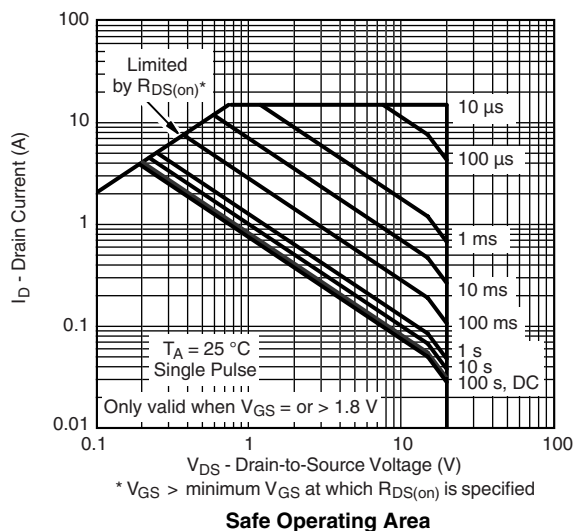
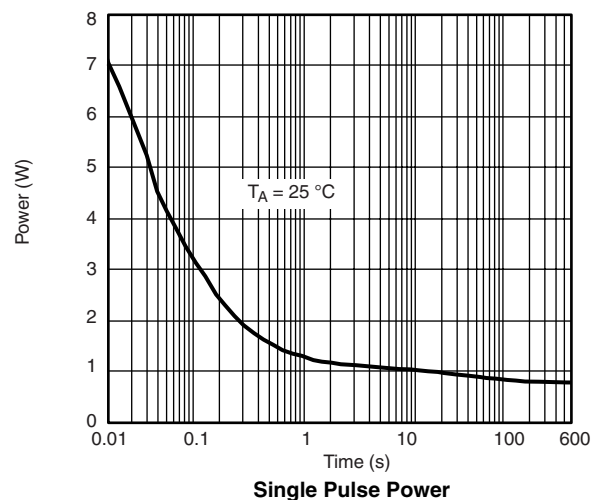
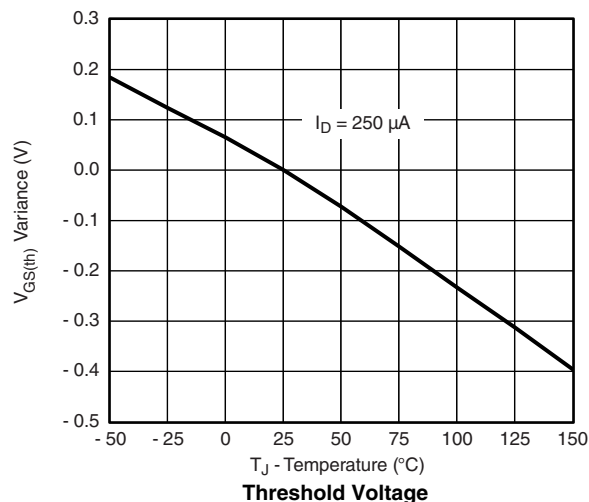
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

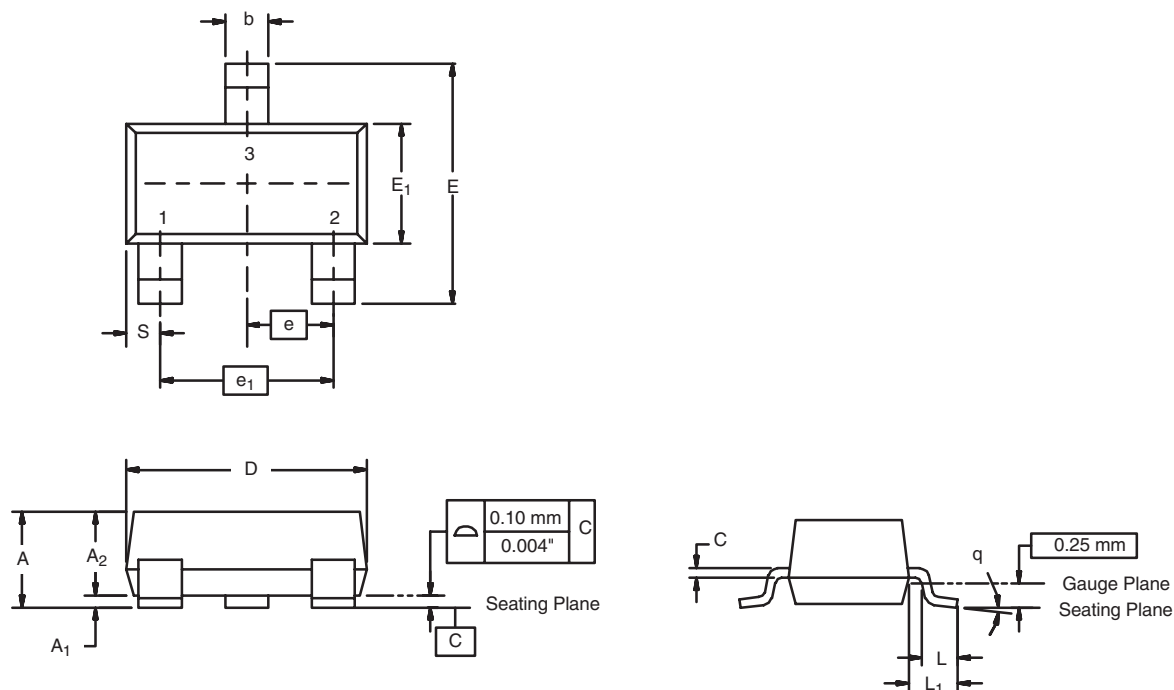


On-Resistance vs. Gate-to-Source Voltage

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

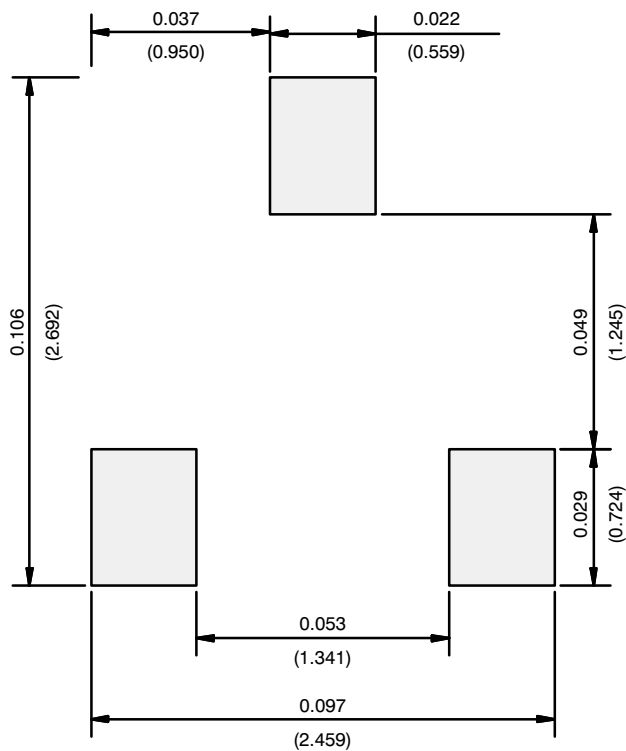
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## SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A <sub>1</sub>	0.01	0.10	0.0004	0.004
A <sub>2</sub>	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E <sub>1</sub>	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e <sub>1</sub>	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L <sub>1</sub>	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01				
DWG: 5479				

## RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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